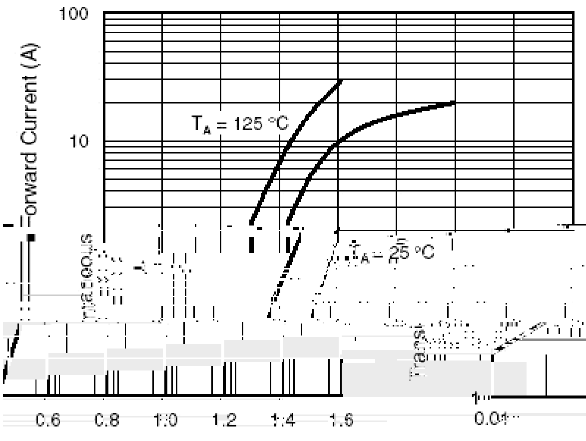
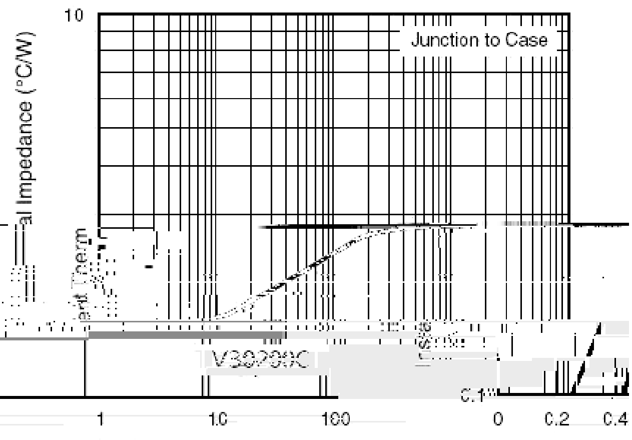
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
Average Rectified Forward Current	$I_{F(AV)}$	2×15	A
Non Repetitive Peak Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Case	R_{Jc}	4.6	/W
Junction and Storage Temperature Range	T_j T_{stg}	-40 +150	

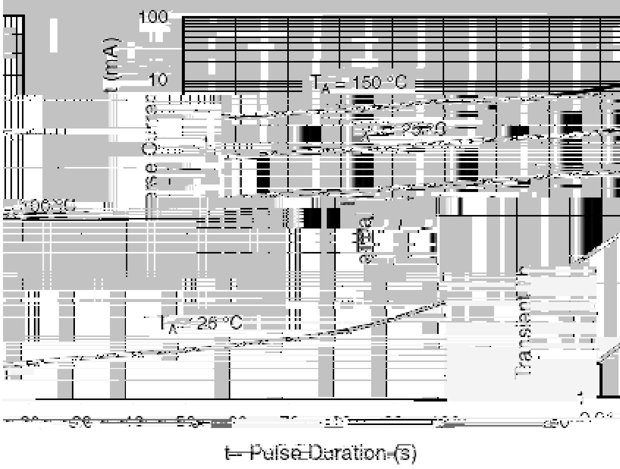
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Reverse Voltage	V_{BR}	I_R=1mA(Ta=25)	200			V
Forward Voltage	V_F	I_F =5A(Ta=25)		0.73	0.85	V
		I_F =10A(Ta=25)		0.80	0.95	V
		I_F =15A(Ta=25)		0.92	1.15	V
		I_F =5A(Ta=125)		0.58		V
		I_F =10A(Ta=125)		0.66		V
		I_F =15A(Ta=125)		0.71	0.85	V
Instantaneous Reverse Current	I_R Note 1	V_R=200V(Ta=25)		4	20	A
		V_R=200V(Ta=125)		5	10	mA

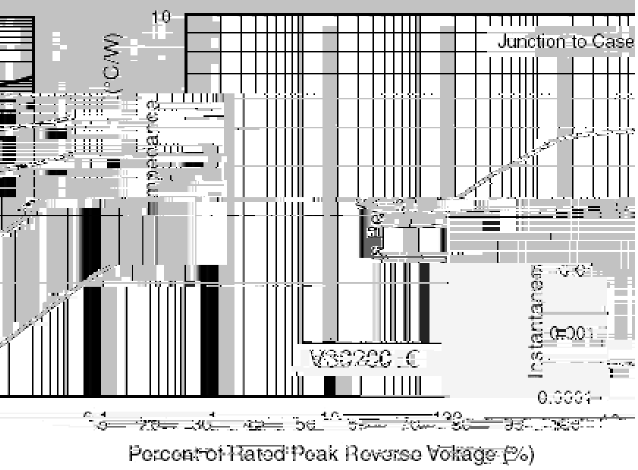
/Notes

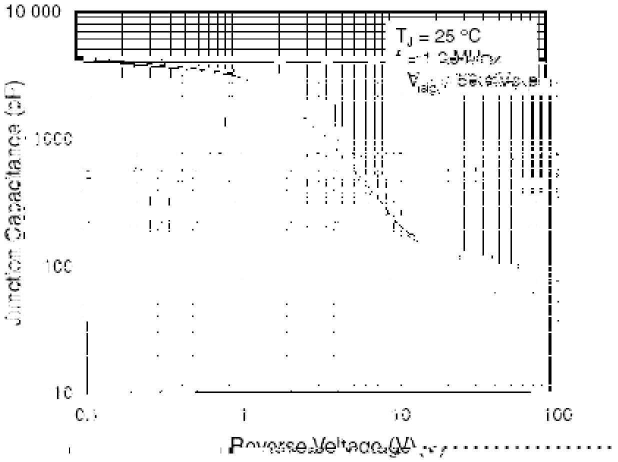
1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip


100
10
Forward Current (A)
TA = 125 °C
TA = 25 °C
0.6
0.8
1.0
1.2
1.4
1.6
Instantaneous Forward Voltage (V)


10
Junction to Case
al Impedance (°C/W)
V30200C
0.01
0.1
1
10
100
t - Pulse Duration (s)

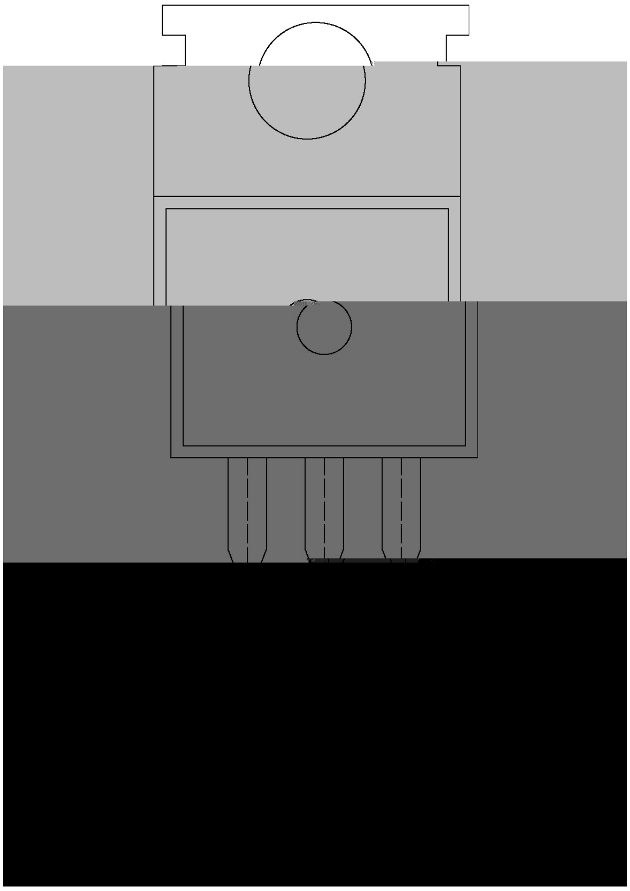

100
10
(mA)
TA = 150 °C
TA = 25 °C
t - Pulse Duration (s)

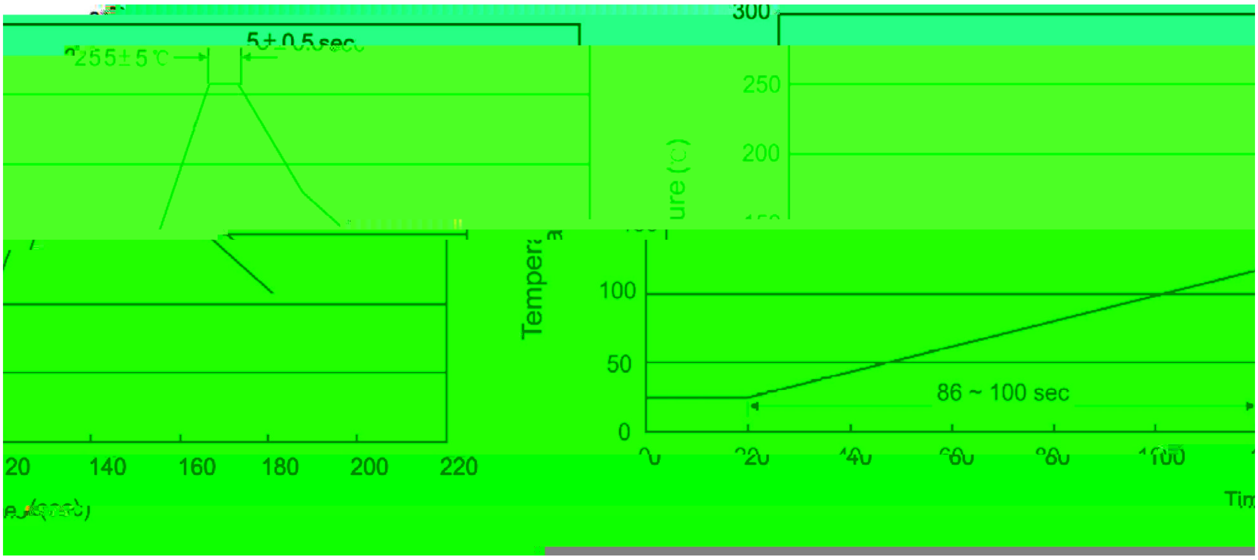

10
Junction to Case
(°C/W)
Transient
V30200C
0.01
0.001
0.0001
Percent of Rated Peak Reverse Voltage (%)


10 000
1000
100
10
Junction Capacitance (pF)
TJ = 25 °C
f = 1.0 MHz
Vsig = 50 mVp-p
0.1
1
10
100
Reverse Voltage (V)

[redacted]

[redacted]





1 25 150 60 90sec;

Note:

1.Preheating:25~150